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INTERNATIONAL Co., LTD.

MX23J32GL0

32G-BIT ROM TYPE GAME CARD MEMORY DATASHEET

Contents

1. FEATURES	4
2. GENERAL DESCRIPTION	4
3. PIN CONFIGURATIONS.....	5
4. PIN DESCRIPTION.....	5
5. BLOCK DIAGRAM	6
Figure 1. Block Diagram	6
6. CARD STATUS DEFINITION	7
Table 1. Card Status	7
7. ID DEFINITION	8
Table 2. RD_ID1/t1RD_ID1	8
Table 3. RD_ID2/t1RD_ID2.....	8
Table 4. RD_ID3/t1RD_ID3.....	8
8. RES DEFINITION	9
Table 5. RD_SELF_REFRESH.....	9
Table 6. RD_REFRESH_STATUS	9
9. ABSOLUTE MAXIMUM RATINGS.....	10
10. RECOMMENDED OPERATING CONDITIONS	10
11. DC CHARACTERISTICS.....	11
Table 7. DC Characteristics ($T_A = 0\sim 60^{\circ}\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$).....	11
Figure 2. Standby Current (ISTB1)	12
Figure 3. Standby Current (ISTB2)	12
12. CAPACITANCE	13
Table 8. Capacitance ($T_A = 0\sim 60^{\circ}\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$, $f = 1.0\text{MHz}$)	13
13. AC CHARACTERISTICS.....	13
Table 9. AC TEST CONDITION	13
Table 10. AC Characteristics (25MHz, $T_A = 0\sim 60^{\circ}\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$).....	14
Table 11. AC Characteristics for RESB Timing ($T_A = 0\sim 60^{\circ}\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$).....	15
Figure 4. RESB Timing Waveform (Case1)	15
Figure 5. RESB Timing Waveform (Case 2)	16



Figure 6. Command Input and Data Output Timing Waveform (Read, 25MHz)	17
Figure 7. Ready/Busy Timing Waveform (Read, 25MHz)	17
Figure 8. Standby Mode Timing Waveform	17
14. POWER SUPPLY DECOUPLING.....	18
15. PACKAGE INFORMATION	19

1. FEATURES

- Voltage Supply
 - VCC : 3.1V
 - VCCIO : 1.8V
- Organization
 - 4096M x 8bit
- Read Operation
 - Page Size: 512 Byte
 - Read Cycle Time: 40ns (Min.)
- Current
 - Read: 115mA
 - Standby: 300uA
- Command/Address/Data Multiplexed Port
- Security Embedded
- Power On Reset Function
- Package: TSOP(I) 48L

2. GENERAL DESCRIPTION

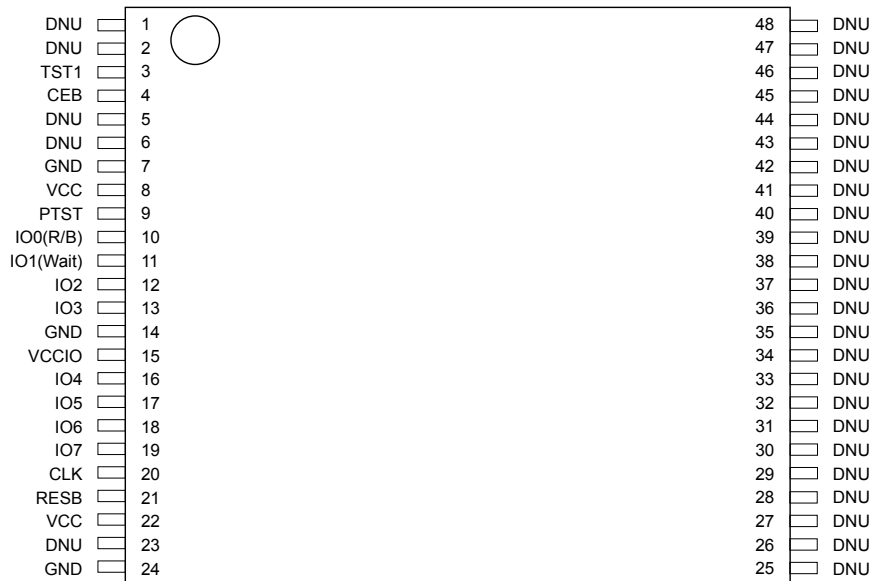
The MX23J32GL0 is a 32Gbit factory pre-programmed XtraROM with 3.1V and IO 1.8V.

It is a bidirectional device, which utilizes the 8 bit multiplexed I/O bus for command, address, and data inputs/outputs.

Simple design structure makes the cost of the device competitive over the other types of code-storage memory IC.

3. PIN CONFIGURATIONS

48 TSOP(I)



4. PIN DESCRIPTION

SYMBOL	TYPE	PIN NAME
CEB	I	Chip Enable Signal 0 : Enable 1 : Disable
IO0	I/O	Command/Address/Data/ReadyBusy Multiplexed I/O Port
IO1	I/O	Command/Address/Data/Wait Multiplexed I/O Port
IO2~IO7	I/O	Command/Address/Data Multiplexed I/O Port
CLK	I	Clock Signal
RESB	I	Reset Signal 0 : Device Reset
TST1	I	Test Pin (Note 1)
PTST	I	Test Pin (Note 1)
VCC	I	Power (3.1V, for Internal Core)
VCCIO	I	Power (1.8V, for I/O)
GND	I	Ground
DNU	-	Non Connection (Note 1)

Note 1: TST1, PTST and DNU pins can be connected to GND, VCC or Open.

5. BLOCK DIAGRAM

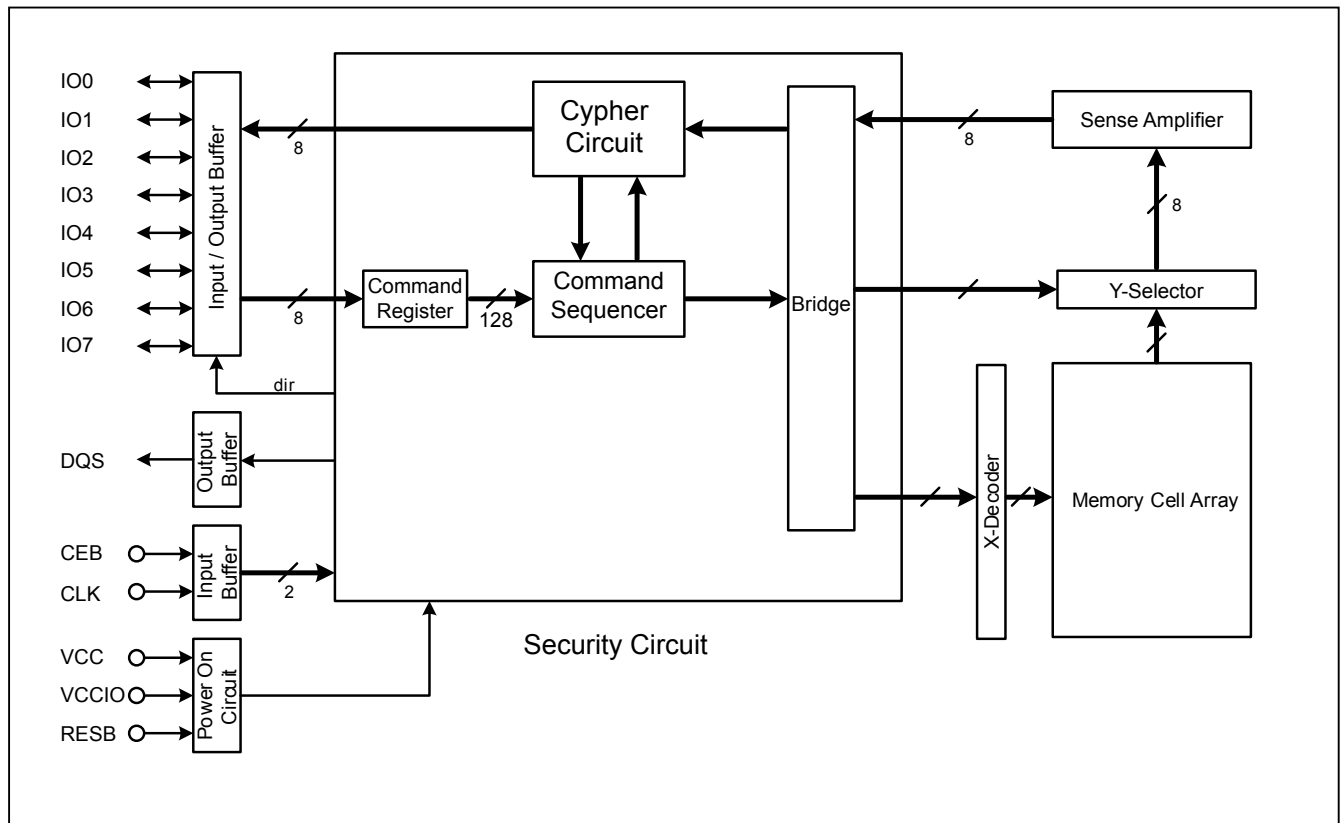


Figure 1. Block Diagram

6. CARD STATUS DEFINITION

Table 1. Card Status

Bit	Values
bit0	CRC Error Flag 0: No Error 1: Error
bit1	0
bit2	Fatal Error Flag 0: No Error 1: Error
bit3	0
bit4-7	0h

7. ID DEFINITION

Table 2. RD_ID1/t1RD_ID1

	Encoding	ID1
Byte0	Maker Code	C2h
Byte1	Memory Size	F0h
Byte2	Options1	01h
Byte3	Memory Type	01h (Note1)

Note1: bit7 *Reserved = 0*
bit6 *Reserved = 0*
bit5 *0: tRB_5 ≤ 100us*
 1: tRB_5 > 100us
bit4 *Reserved = 0*
bit3 *0: ROM Type*
 1: R/W Type
bit2 *Reserved = 0*
bit[1:0] *00: Reserved*
 01: T1
 10: T2
 11: Reserved

Table 3. RD_ID2/t1RD_ID2

	Encoding	ID2
Byte0	Options1	02h
Byte1	Options2	00h
Byte2	Options3	00h
Byte3	Options4	00h

Table 4. RD_ID3/t1RD_ID3

	Encoding	ID3
Byte0	Options1	00h
Byte1	Options2	00h
Byte2	Options3	00h
Byte3	Options4	00h

8. RES DEFINITION**Table 5. RD_SELF_REFRESH**

	Encoding	RES
Byte0	Response1	00h
Byte1	Response2	00h
Byte2	Response3	00h
Byte3	Response4	00h

Table 6. RD_REFRESH_STATUS

	Encoding	RES
Byte0	Response1	FFh
Byte1	Response2	00h
Byte2	Response3	00h
Byte3	Response4	00h

9. ABSOLUTE MAXIMUM RATINGS

ITEM	SYMBOL	RATINGS
Power Supply Voltage1	V_{CC}	-0.5V to 4.6V
Power Supply Voltage2	V_{CCIO}	-0.5V to 2.5V
Input Voltage	V_{IN}	-0.3V to $V_{CC} + 0.3V$ (Note1)
Output Voltage	V_{OUT}	-0.3V to $V_{CC} + 0.3V$ (Note1)
Ambient Operating Temperature	T_{OPR}	0°C to 60°C
Storage Temperature	T_{STG}	-25°C to 85°C

(Note1):

Minimum DC voltage on input or I/O pins is -0.3V. During voltage transitions, inputs may undershoot GND to -1.3V for periods of up to 20ns.

Maximum DC voltage on input or I/O pins is $V_{CC} + 0.3V$. During voltage transitions, inputs may overshoot V_{CC} to $V_{CC} + 2.0V$ for periods of up to 20ns.

10. RECOMMENDED OPERATING CONDITIONS

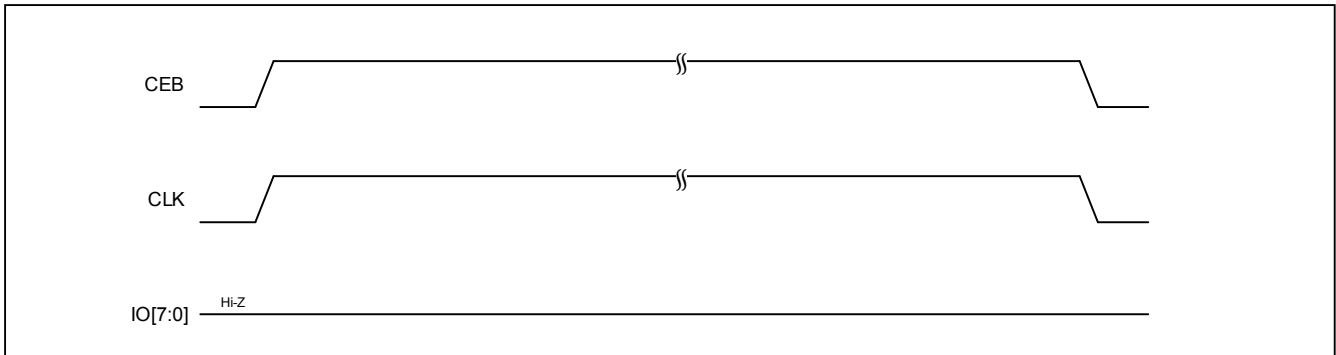
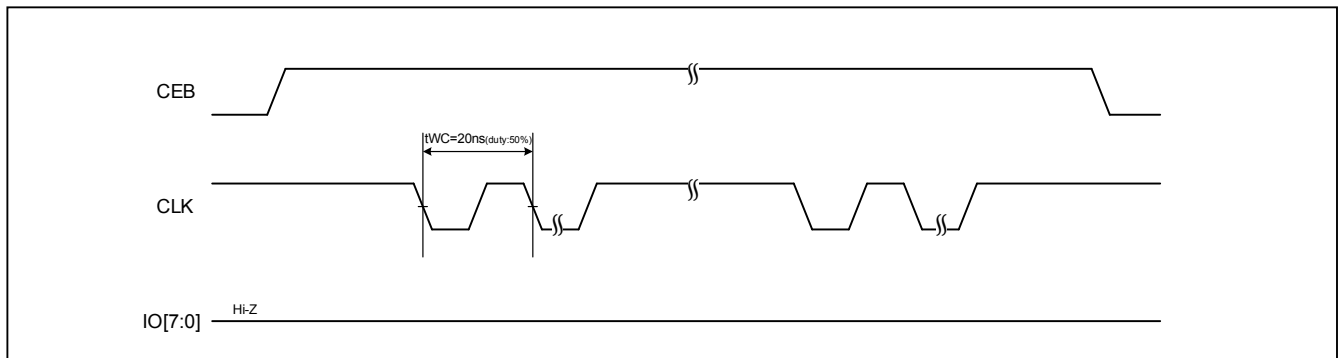
ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT
Operating Temperature	T_A	0	25	60	°C
Power Supply Voltage	V_{CC}	2.8	3.1	3.6	V
IO Power Supply Voltage	V_{CCIO}	1.62	1.8	1.98	V

11. DC CHARACTERISTICS

Table 7. DC Characteristics ($T_A = 0\sim 60^\circ\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$)

ITEM	SYMBOL	TEST CONDITIONS		MIN.	MAX.	UNIT
Input High Voltage	V_{IH}	-		$0.75 * V_{CCIO}$	$V_{CCIO} + 0.3$	V
Input Low Voltage	V_{IL}	-		-0.3	$0.3 * V_{CCIO}$	V
Schmitt Trigger Input (L to H) (CLK, CEB)	V_{t+}	-		-	$0.7 * V_{CCIO}$	V
Schmitt Trigger Input (H to L) (CLK, CEB)	V_{t-}	-		$0.3 * V_{CCIO}$	-	V
Schmitt Trigger Hysteresis Voltage (CLK, CEB)	$(\Delta)V_t$	-		0.15	-	V
Output High Voltage	V_{OH}	$I_{OH} = -400\mu\text{A}$		$0.85 * V_{CCIO}$	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 1.6\text{mA}$		-	$0.1 * V_{CCIO}$	V
Operating Current 1	I_{CC}	$t_{WC}=40\text{ns}$		-	115	mA
Operating Current 2	I_{CCIO}	$t_{WC}=40\text{ns}$		-	20	mA
Standby Current 1-1	I_{CC_STB1}	CEB= $V_{CCIO} - 0.2\text{V}$, IO= $V_{CCIO} \pm 0.2\text{V}$, CLK= $V_{CCIO} - 0.2\text{V}$	$T_A=25^\circ\text{C}$	-	180	μA
			$T_A=60^\circ\text{C}$	-	300	μA
Standby Current 1-2	I_{CCIO_STB1}	CEB= $V_{CCIO} - 0.2\text{V}$, IO= $V_{CCIO} \pm 0.2\text{V}$, CLK= $V_{CCIO} - 0.2\text{V}$	$T_A=25^\circ\text{C}$	-	30	μA
			$T_A=60^\circ\text{C}$	-	50	μA
Standby Current 2-1	I_{CC_STB2}	CEB= $V_{CCIO} - 0.2\text{V}$, IO= $V_{CCIO} \pm 0.2\text{V}$, $t_{WC}=40\text{ns}$ $t_{WH}=20\text{ns}$, $t_{WL}=20\text{ns}$	$T_A=25^\circ\text{C}$	-	180	μA
			$T_A=60^\circ\text{C}$	-	300	μA
Standby Current 2-2	I_{CCIO_STB2}	CEB= $V_{CCIO} - 0.2\text{V}$, IO= $V_{CCIO} \pm 0.2\text{V}$, $t_{WC}=40\text{ns}$ $t_{WH}=20\text{ns}$, $t_{WL}=20\text{ns}$	$T_A=25^\circ\text{C}$	-	30	μA
			$T_A=60^\circ\text{C}$	-	50	μA
Input Leakage Current	I_{LI}	$V_{IN} = 0 \text{ to } V_{CCIO} (\text{max})$		-	± 10	μA
Output Leakage Current	I_{LO}	$V_{OUT} = 0 \text{ to } V_{CCIO} (\text{max})$		-	± 10	μA

Note: only happen during the 1st page read of boundary, other pages will not.

**Figure 2. Standby Current (ISTB1)****Figure 3. Standby Current (ISTB2)**

12. CAPACITANCE

Table 8. Capacitance ($T_A = 0\sim 60^\circ\text{C}$, $V_{CC} = 2.8\sim 3.6\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$, $f = 1.0\text{MHz}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNIT
Output Capacitance	C_{OUT}	$V_{OUT} = 0\text{V}$	-	10	pF
Input Capacitance	C_{IN}	$V_{IN} = 0\text{V}$	-	10	pF

13. AC CHARACTERISTICS

Table 9. AC TEST CONDITION

PARAMETER	TEST CONDITIONS
Input Pulse Level	$V_{CCIO} * 0.1$ to $V_{CCIO} * 0.9$
Input Rise and Fall Times	3ns
Input Timing Levels (CLK)	$V_{CCIO} * 0.5$
Input Timing Levels (CEB, IO, RESB)	$V_{CCIO} * 0.3$ to $V_{CCIO} * 0.7$
Output Timing Levels	0.45V to $V_{CCIO} - 0.45\text{V}$
Output Load	30pF

Note: $V_{CCIO} = 1.62\text{V}\sim 1.98\text{V}$

Table 10. AC Characteristics (25MHz, T_A = 0~60°C, V_{CC} = 2.8~3.6V, V_{CCIO} = 1.62~1.98V)

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT
CLK Cycle Time		tWC	38	40	-	ns
CLK High Pulse Width		tWH	18	20	-	ns
CLK Low Pulse Width		tWL	18	20	-	ns
CEB Setup Time		tCS	120	-	-	ns
CEB Hold Time		tCH	165	-	-	ns
CEB High Pulse Width		tCEPH	300	-	-	ns
Data Setup Time		tDS	10	-	-	ns
Data Hold Time		tDH	4	-	-	ns
Data Valid Time		tDV	0	-	-	ns
CLK Access Time		tREA	0	-	27	ns
Ready/Busy1	RD_ID1	tRB_N1	2			cycle
	RD_ID2	tRB_N2	2			cycle
	RD_ID3	tRB_N3	2			cycle
	CHG_INIT	tRB_N4	2			cycle
	RD_PAGE	tRB_N5	-	-	100	us
	RD_SELF_REFRESH	tRB_N6	2			cycle
	RD_REFRESH_STATUS	tRB_N7	2			cycle
	iRD_INIT	tRB_I1	-	-	200	us
	iSET_INIT1	tRB_I2	314			cycle
	iSET_GEN_RAND	tRB_I3	-	-	50	us
	iSET_INIT2	tRB_I4	314			cycle
	t1RD_ID1	tRB_S1	18	-	24	cycle
	t1RD_ID2	tRB_S2	18	-	24	cycle
	t1RD_ID3	tRB_S3	18	-	24	cycle
	t1RD_UID	tRB_S4	-	-	100	us
	t1RD_PAGE	tRB_S5	-	-	100	us
	t1RD_REFRESH	tRB_S6	26			cycle
	t1RD_SET_KEY	tRB_S7	314			cycle
Ready/Busy2	RD_PAGE	tRB2_N1	2 cycle	-	40	us
	t1RD_PAGE	tRB2_S1	2 cycle	-	40	us
CEB High to Output Hi-Z Time (Note1)		tCHZ	-	-	30	ns
Output to Hi-Z Time (Note1)		tDHZ	-	-	38	ns
Latency1		tHZ1	2			cycle
Latency2		tHZ2	1			cycle
Latency3		tHZ3	1			cycle
Active to Standby Time (Note1)		tAST	-	-	300	ns

Note1: This spec is guaranteed with design specification, not tested.

Note2: tRB_* and tRB2_* are based on Wait=0cycle.

Table 11. AC Characteristics for RESB Timing ($T_A = 0 \sim 60^\circ\text{C}$, $V_{CC} = 2.8 \sim 3.6\text{V}$, $V_{CCIO} = 1.62 \sim 1.98\text{V}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
RESB Non-Active Time	tRNA	9	-	-	us
RESB Low Time 1	tRES1	100	-	-	us
RESB High Time 1	tRH1	250	-	-	ms
RESB Setup Time	tRS	100	-	-	ns
RESB Low Time 2	tRES2	1	-	-	us
RESB High Time 2	tRH2	250	-	-	ms

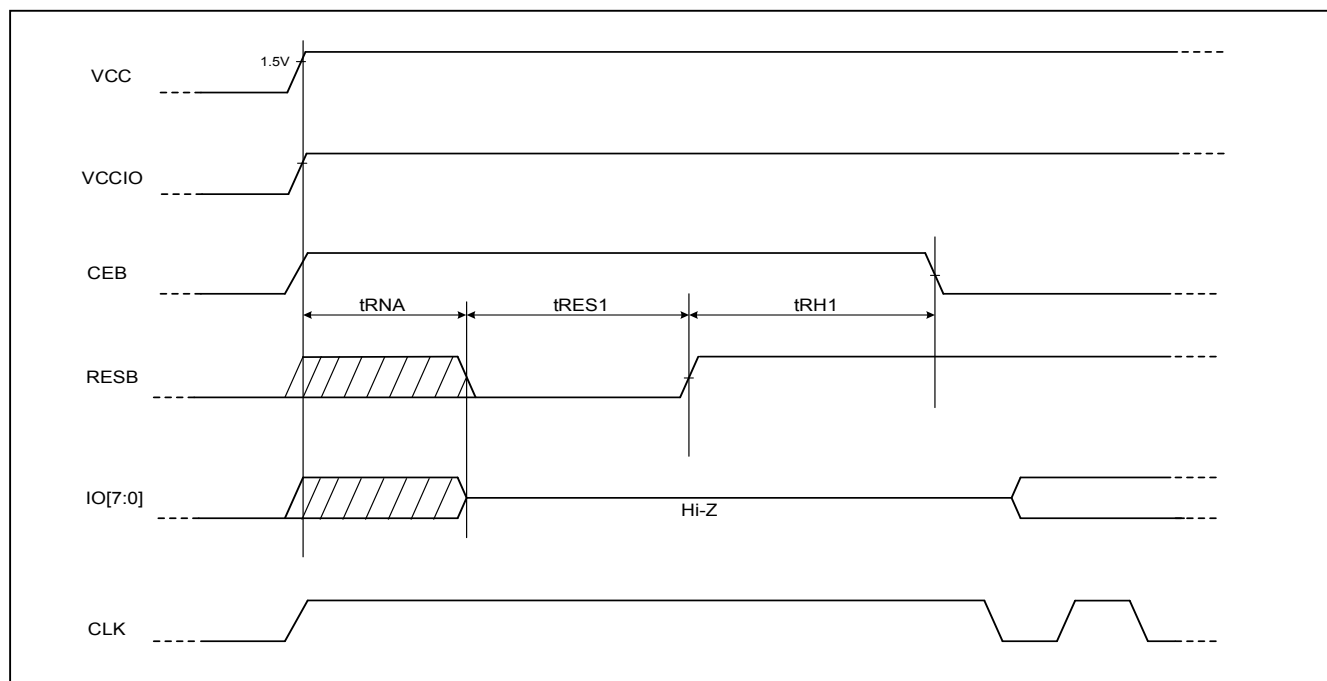


Figure 4. RESB Timing Waveform (Case1)

Note 1: During "RESB=L", IO7~IO0 is Hi-Z.

Note 2: RESB from low to high will triggered POR function during tRH1.

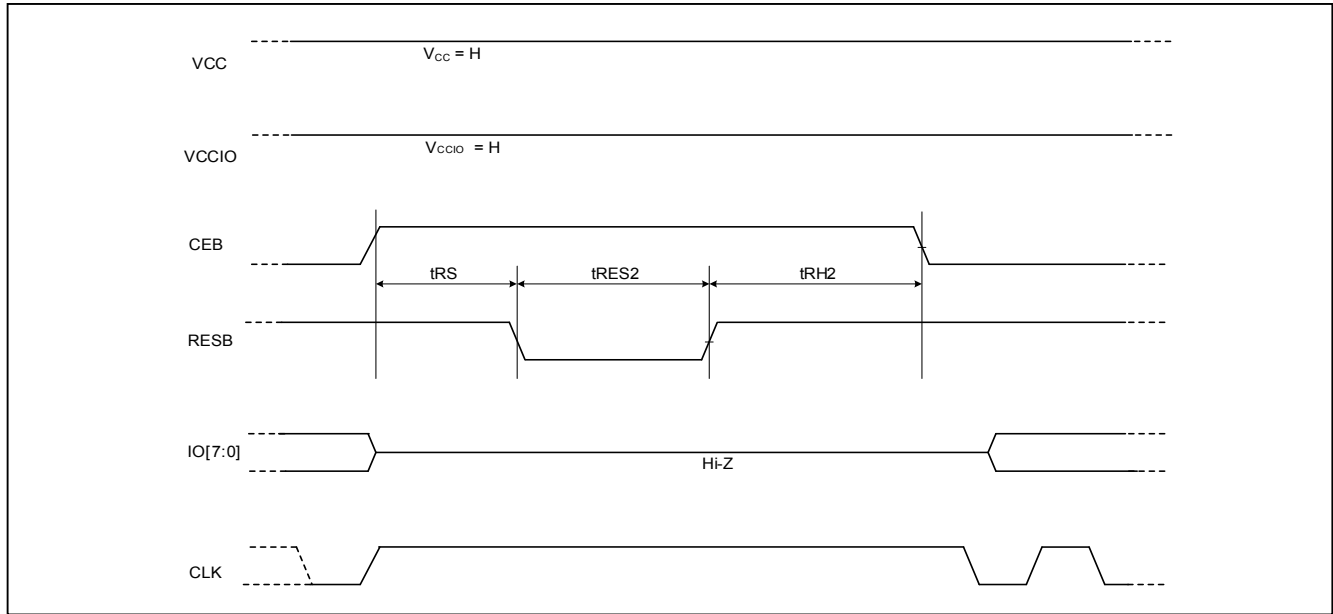


Figure 5. RESB Timing Waveform (Case 2)

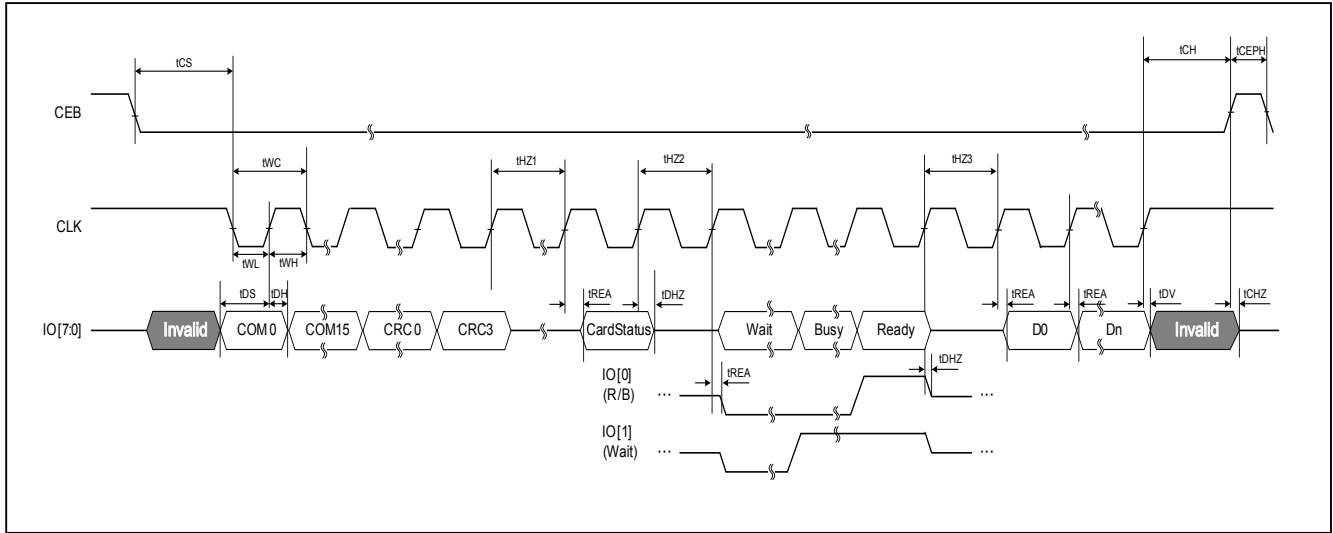


Figure 6. Command Input and Data Output Timing Waveform (Read, 25MHz)

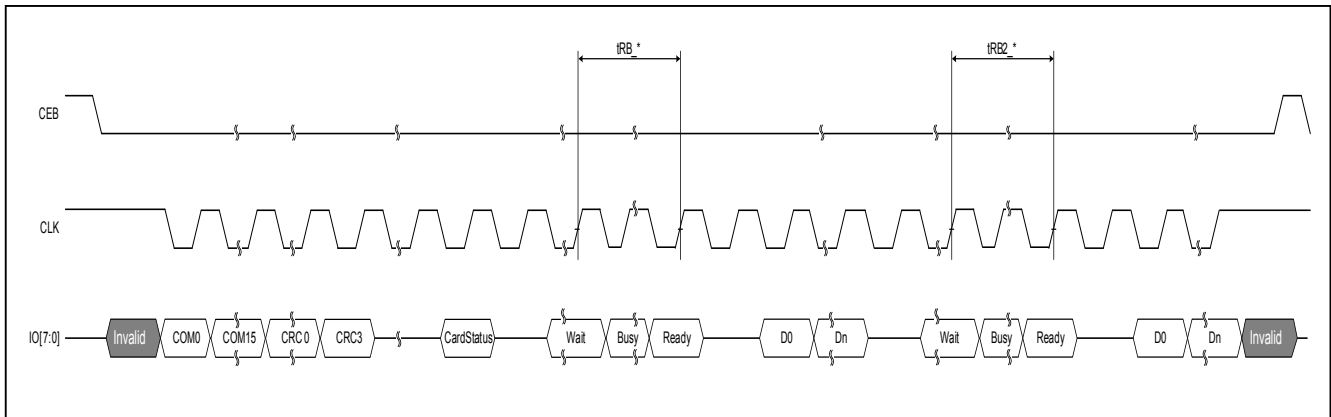


Figure 7. Ready/Busy Timing Waveform (Read, 25MHz)

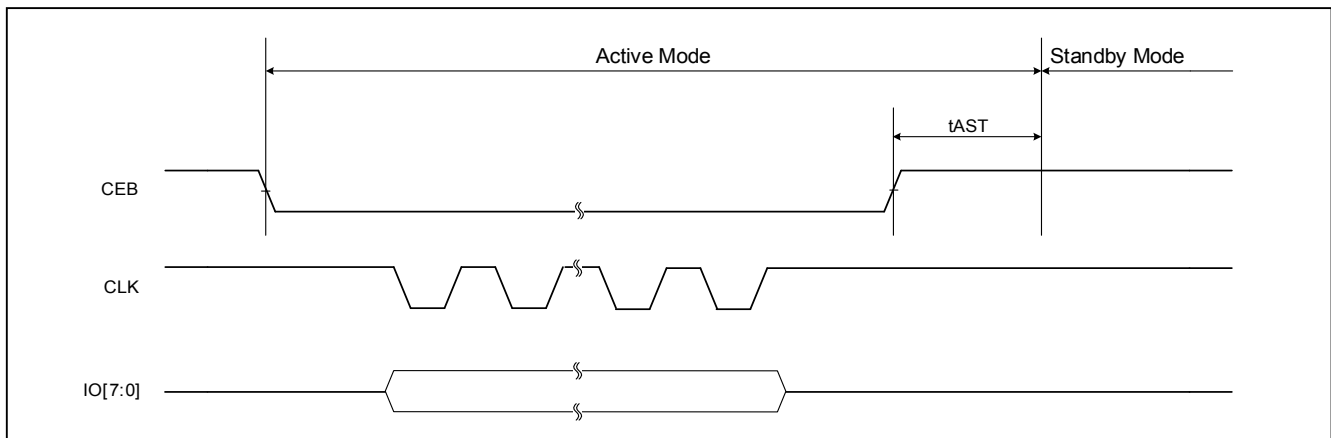


Figure 8. Standby Mode Timing Waveform



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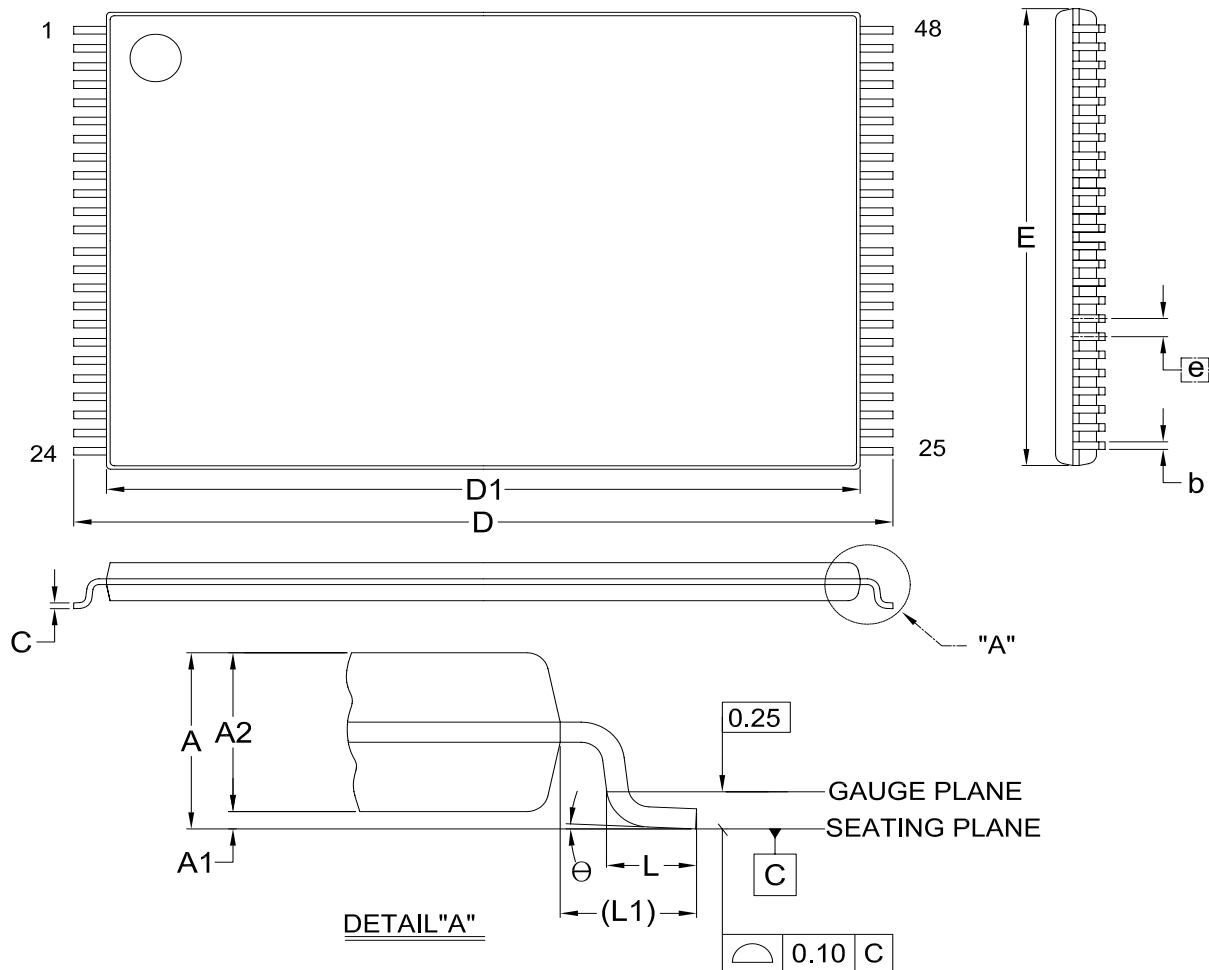
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14. POWER SUPPLY DECOUPLING

In order to reduce power noise, please connect 0.1uF ceramic capacitor between power (VCC and VCCIO) and ground.

15. PACKAGE INFORMATION

Doc. Title: Package Outline for TSOP(I) 48L (12X20mm)NORMAL FORM



Dimensions (inch dimensions are derived from the original mm dimensions)

SYMBOL		A	A1	A2	b	C	D	D1	E	e	L	L1	Θ
UNIT													
mm	Min.	—	0.05	0.95	0.17	0.10	19.80	18.30	11.90	—	0.50	0.70	0°
	Nom.	—	0.10	1.00	0.20	0.13	20.00	18.40	12.00	0.50	0.60	0.80	5°
	Max.	1.20	0.15	1.05	0.27	0.21	20.20	18.50	12.10	—	0.70	0.90	8°
Inch	Min.	—	0.002	0.037	0.007	0.004	0.780	0.720	0.469	—	0.020	0.028	0°
	Nom.	—	0.004	0.039	0.008	0.005	0.787	0.724	0.472	0.020	0.024	0.031	5°
	Max.	0.047	0.006	0.041	0.011	0.008	0.795	0.728	0.476	—	0.028	0.035	8°

Dwg. No.	Revision	Reference			
		JEDEC	EIAJ		
6110-1607	10	MO-142			



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